

GSE050LU2NTF

ESD Protection Diode

Product Description

It is designed to protect sensitive electronics from damage due to electrostatic discharge (ESD) and other transient events.

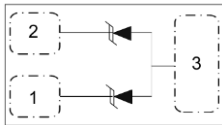
Features

- Operating Voltage: 5V.
- Unidirectional Configurations
- IEC61000-4-2(ESD) $\pm 15\text{kV}$ (Air)
- IEC61000-4-2(ESD) $\pm 15\text{kV}$ (Contact)
- IEC61000-4-4(EFT) 40A (5/50ns)
- IEC61000-4-5(Lighting) 3.5A (8/20 μs)

Mechanical Data

- DFN1006-3L(A) Package
- RoHS Compliant and Halogen Free

Package and Pin Assignment

DFN1006-3L(A)			Equivalent Circuit		
					
Pin	Symbol	Description	Pin	Symbol	Description
1	K1	Cathode 1	2	K2	Cathode 2
3	A	Common Anode			

Ordering and Marking Information

GS P/N	Package	Marking	Quantity / Reel
GSE050LU2NTF	DFN1006-3L(A)	L	10,000PCS
GSE050LU2NTF - Product Code: GSE050LU2 - Package Code: NT for DFN1006-3L(A) - Green Level: F for RoHS Compliant and Halogen Free			
Marking Information			
		- Product Code: L • Dot denotes Pin 1	

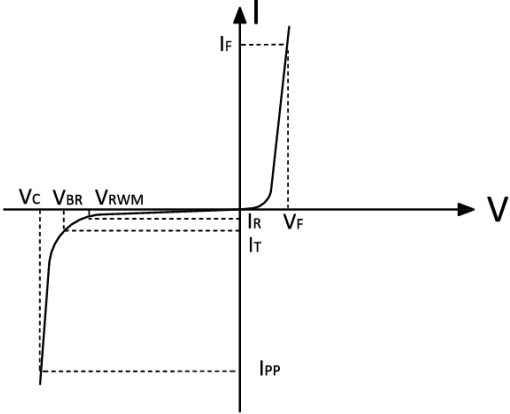
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit
P _{PP}	Peak Pulse Power (t _p =8/20μs)	40	W
I _{PP}	Peak Pulse Current (t _p =8/20μs)	3.5	A
V _{ESD}	ESD Per IEC61000-4-2 (Air)	±15	KV
	ESD Per IEC61000-4-2 (Contact)	±15	KV
T _J	Operating Junction Temperature Range	-55 to +125	°C
T _{STG}	Storage Temperature Range	-55 to +1125	°C

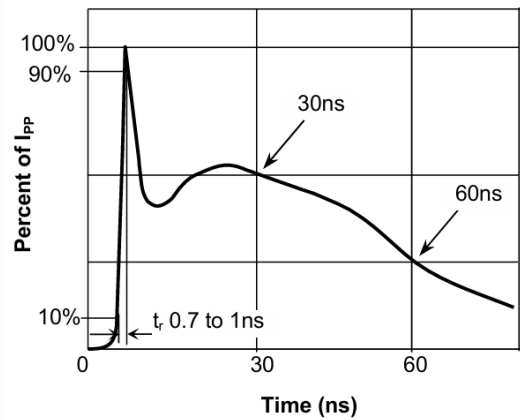
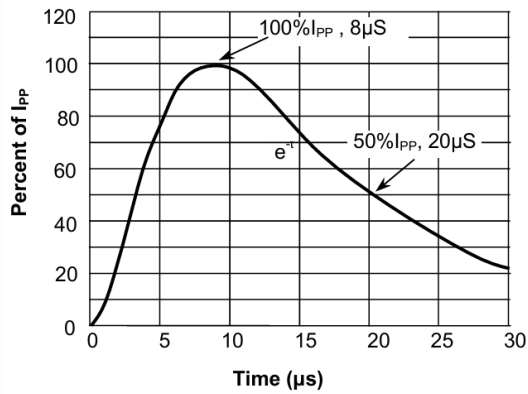
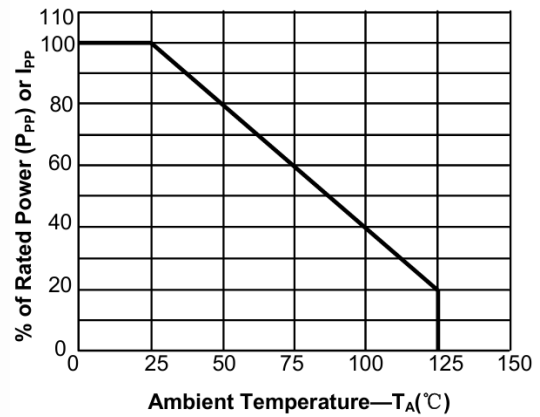
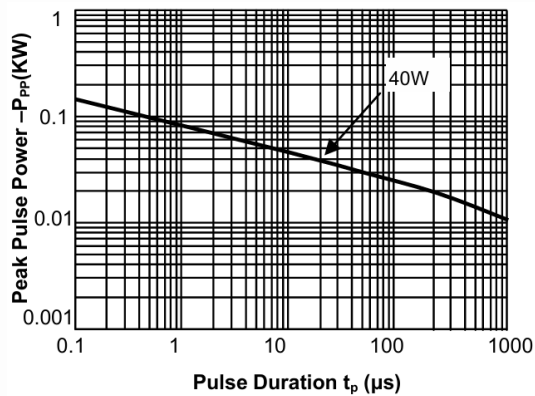
Electrical Characteristics (T_A=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{RWM}	Reverse Working Voltage	-			5	V
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA	5.6			V
I _R	Reverse Leakage Current	V _{RWM} =5V			0.1	μA
V _C	Clamping Voltage	I _{PP} =3A (8/20μs)			13.5	V
C _J	Junction Capacitance	V _R =0V, f=1MHz		0.3		pF

Electrical Parameters

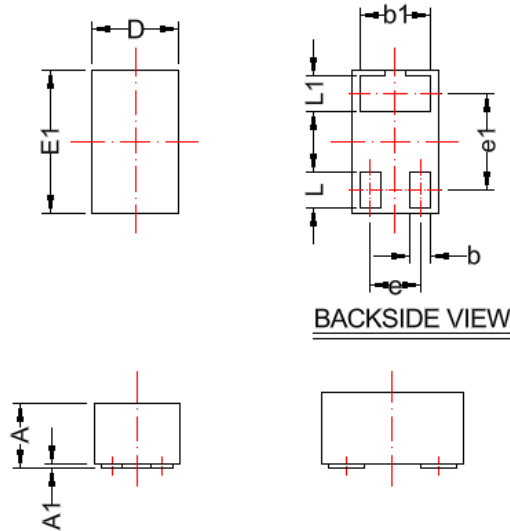
Symbol	Parameter	
I _{PP}	Reverse Peak Pulse Current	
V _C	Clamping Voltage @ I _{PP}	
V _{RWM}	Reverse Working Voltage	
I _R	Reverse Leakage Current @ V _{RWM}	
V _{BR}	Breakdown Voltage @ I _T	
I _T	Test Current	

Typical Characteristics (T_A=25°C unless otherwise specified)

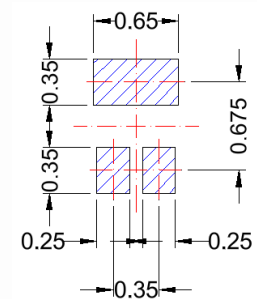


DFN1006-3L(A)

Package Dimension



Recommended Land Pattern



Unit:mm

Dimensions				
Symbol	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	0.40	0.50	0.016	0.020
A1	0.00	0.05	0.000	0.002
b	0.10	0.20	0.004	0.008
b1	0.40	0.60	0.016	0.024
D	0.55	0.65	0.022	0.026
E1	0.95	1.05	0.037	0.041
e	0.350 BSC		0.014 BSC	
e1	0.675 BSC		0.027 BSC	
L	0.20	0.40	0.008	0.016
L1	0.20	0.30	0.008	0.012

NOTE:

Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.

NOTICE

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